

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





Product data sheet

### 1. General description

Silicon Carbide Schottky diode in a SOD59A (TO-220AC) plastic package, designed for high frequency switched-mode power supplies.

### 2. Features and benefits

- Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

## 3. Applications

- Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

## 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	-	650	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 120 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>		-	-	8	A
Tj	junction temperature			-	-	175	°C
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>		-	1.5	1.7	V





### **NXP Semiconductors**

## NXPSC08650

#### Silicon Carbide Diode

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic chara	acteristics					
Qr	recovered charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$	-	13	-	nC

## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K-K-A
2	А	anode	205	001aaa020
mb	mb	mounting base; connected to cathode	<b>TO-220AC (SOD59A)</b>	

## 6. Ordering information

### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NXPSC08650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
NXPSC08650	NXPSC08650

Silicon Carbide Diode

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	650	V
V <sub>RWM</sub>	crest working reverse voltage		-	650	V
V <sub>R</sub>	reverse voltage	DC	-	650	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 120 °C; square-wave pulse; Fig. 1; Fig. 2	-	8	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 120 °C; square-wave pulse	-	16	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	48	A
		$t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	-	385	A
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

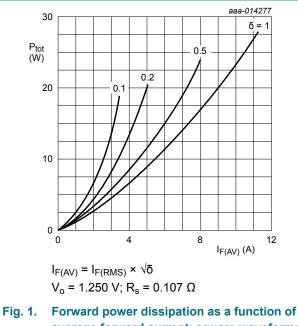


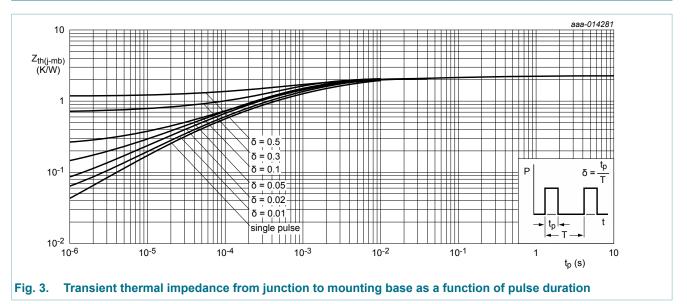


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

Silicon Carbide Diode

### 9. Thermal characteristics

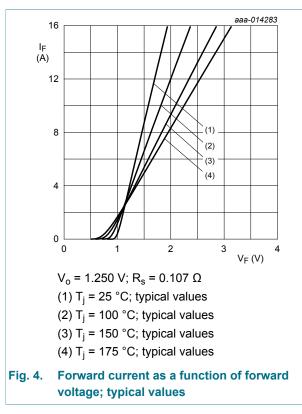
Table 6. T	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 3	-	-	2.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

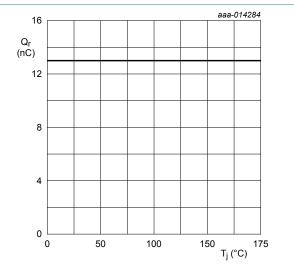


Silicon Carbide Diode

### **10. Characteristics**

Table 7. C	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics					
V <sub>F</sub> forward	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.5	1.7	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	1.8	2.1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C	-	-	230	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C	-	-	700	μA
Dynamic ch	naracteristics					
Q <sub>r</sub>	recovered charge	$I_{F} = 8 \text{ A; } dI_{F}/dt = 500 \text{ A}/\mu\text{s; } V_{R} = 400 \text{ V;}$ $T_{j} = 25 \text{ °C; } \frac{\text{Fig. 5}}{5}$	-	13	-	nC
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C	-	260	-	pF
		f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C	-	30	-	pF
		f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	24	-	pF



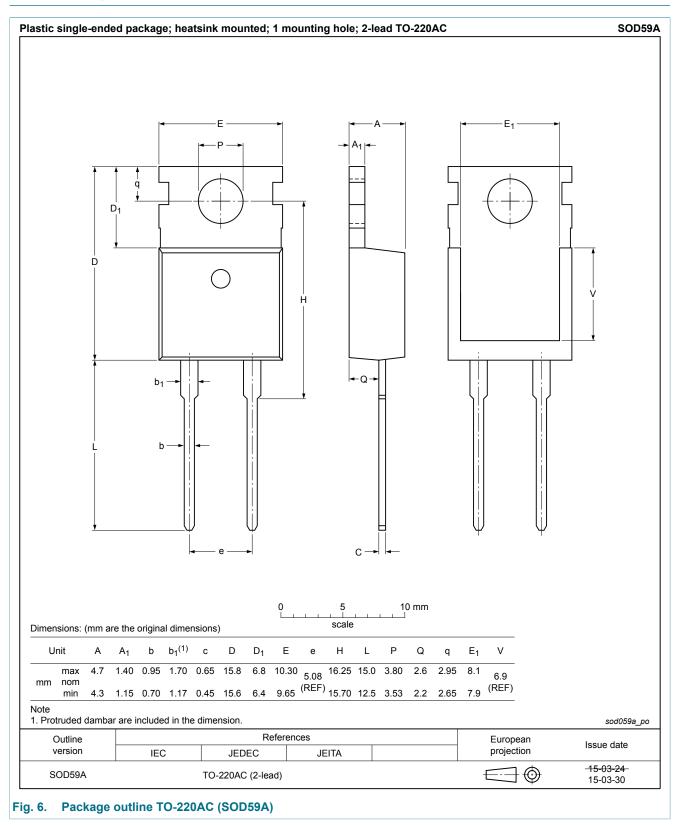






Silicon Carbide Diode

### **11. Package outline**



NXPSC08650

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#### Silicon Carbide Diode

#### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### Silicon Carbide Diode

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